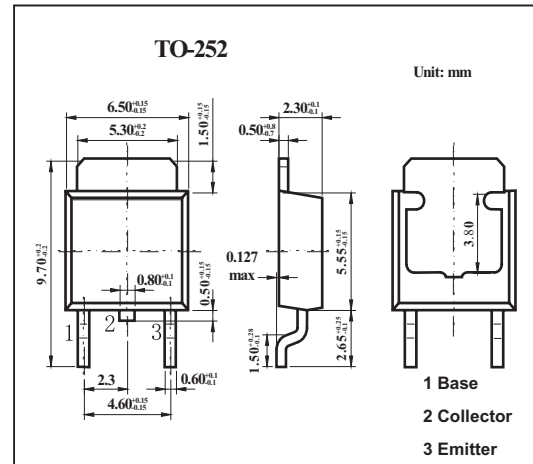


NPN Silicon Epitaxial Transistor

2SC3632-Z

■ Features

- High voltage $V_{CE0}=600V$
- High speed $t_f < 0.5\mu s$

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	600	V
Collector to emitter voltage	V_{CES}	600	V
Emitter to base voltage	V_{EBO}	7	V
Peak collector current *1	I_{CP}	2	A
Collector current	I_C	1	A
Total power dissipation $T_a = 25^\circ C * 2$	P_T	2	W
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

*1 $p_w \leq 10ms$, Duty cycle $\leq 50\%$

*2 when mounted on ceramic substrate of $7.5cm^2 \times 0.7mm$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
colleotr cutoff current	I_{CBO}	$V_{CB}=600V, I_E=0$			10	μA
Emitter cutoff current	I_{EBO}	$V_{EB}=7V, I_C=0$			10	μA
DC Current Gain	hFE	$V_{CE}=5V, I_C=100mA$	30	55	120	
		$V_{CE}=5V, I_C=100mA$	5	7		
Collector saturation voltage	$V_{CE(sat)}$	$I_C=400mA, I_B=80mA$		0.35	1.0	V
Base to saturation voltage	$V_{BE(sat)}$	$I_C=400mA, I_B=80mA$		0.9	1.2	V
Gain Bandwidth Product	fT	$V_{CE}=5V, I_E=-50mA$		30		MHz
Output capacitance	cob	$V_{CB}=10V, I_E=0A, f=1MHz$		14		pF
Turn-on time	t_{on}	$I_C=0.5A, R_L=500\Omega$		0.1	0.5	μs
Storage time	t_{stg}	$I_{B1}=-I_{B2}=0.1A$		4.0	5.0	μs
Fall time	t_f	$V_{CC}=250V$		0.2	0.5	μs

■ hFE Classification

Marking	M	L	K
hFE	30 to 60	40 to 80	60 to 120